

**IN THE CLAIMS:**

1. (Currently Amended) A method of reducing the dislocations present in a SiGe heterojunction bipolar transistor, said method comprising ~~the steps of~~:

(a) providing a semiconductor substrate comprising a collector region located at an upper surface of said semiconductor substrate and isolation regions adjacent said collector region, said collector region and said isolation regions are located within said semiconductor substrate;

(b) recessing a portion of the isolation regions below ~~an~~ said upper surface of said collector region in said semiconductor substrate so as to provide a recessed isolation surface below said upper surface of the collector region in the semiconductor substrate and a non-recessed surface that is substantially planar with said upper surface of the collector region in the semiconductor substrate; and

(c) forming a SiGe layer on the semiconductor substrate as well as said recessed isolation surface, wherein said recessing controls facet formation at edges at the SiGe layer and the upper surface of the collector.

2. (Original) The method of Claim 1 wherein said isolation regions are trench isolation regions.

3. (Original) The method of Claim 2 wherein said trench isolation regions are formed by lithography, etching and trench filling.

4. (Original) The method of Claim 3 wherein said trench filling includes deposition of  $\text{SiO}_2$ .
5. (Original) The method of Claim 1 wherein a patterned dielectric layer is formed on a portion of said isolation regions prior to conducting step (b).
6. (Previously Presented) The method of Claim 5 wherein said patterned dielectric layer is composed of a nitride.
7. (Original) The method of Claim 1 wherein said recessing includes lithography and etching.
8. (Original) The method of Claim 1 wherein after said recessing a patterned dielectric is formed on a portion of the isolation region that is not recessed.
9. (Original) The method of Claim 1 wherein said SiGe layer is formed by a deposition process selected from the group consisting of ultra-high vacuum chemical vapor deposition (UHVCVD), molecular beam epitaxy (MBE), rapid thermal chemical vapor deposition (RTCVD) and plasma-enhanced chemical vapor deposition (PECVD).
10. (Previously Presented) The method of Claim 1 further comprising the steps of:
  - (d) forming an insulator on said SiGe layer;

(e) providing an opening in said insulator so as to expose a portion of said SiGe layer;

(f) forming an emitter material on said insulator and in said opening so as to contact said SiGe layer; and

(g) patterning said emitter material and said insulator so as to form a patterned emitter and a patterned insulator on said SiGe layer.

Claims 11-19 (Canceled)